# Thyristor with built-in reverse diode for HID lamp ignition TFC561D

## Features

- Repetitive peak off-state voltage: VDRM=600V
- Repetitive peak surge on-state current: ITRM=430A
- Critical rate-of-rise of on-state current: di/dt=1200A/us
- Gate trigger current: IGT=20mA max
- With built-in reverse diode

## **Absolute Maximum Ratings**

Parameter	Symbol	Ratings	Unit	Conditions	
Repetitive peak off-state voltage	VDRM	600	v	Tj=–40 to +125°C, R <sub>GK</sub> =1kΩ	
Repetitive surge peak on-state current	Itrm	430 A		V <sub>D</sub> ≦430V, 100kcycle, <b>*</b> Wp=1.3μs, Ta=125°C	
Critical rate-of-rise of on-state current	di/dt	1200	A/µs	*	
Peak forward gate current	IFGM	2.0	А	f≧50Hz, duty≦10%	
Peak gate power loss	Рдм	5.0	w	f≧50Hz, duty≦10%	
Average gate power loss	PG (AV)	0.5	w		
Peak reverse gate voltage	VRGM	5	v	f≧50Hz	
Diode repetitive peak surge forward current	IFRM	240	А	V <sub>D</sub> ≦430V, 100kcycle,  * Wp=1.3µs, Ta=125°C	
Junction temperature	Tj	-40 to +125	°C		
Storage temperature	Tstg	-40 to +125	°C		

#### External Dimensions (unit: mm)



Weight: Approx. 1.5g

### **Measurement circuit**



\* The surge current for T=10ms /cycle shall be applied 50 cycles successively, and an interval time shall follow to cool down the junction temperature of the device to 125°C. This process shall be repeated up to 100K cycles.

## **Electrical Characteristics**

Electrical Characteristics (Tj=25									
Parameter	Symbol	Ratings			Unit	Conditions			
	Symbol	min	typ	max	Unit	Conditions			
On-state voltage	VTM			1.4	v	IT=10A			
Gate trigger voltage	VGT			1.5	v	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω			
Gate trigger current	IGT			20	mA	V <sub>D</sub> =6V, R <sub>L</sub> =10Ω			
Gate non-trigger voltage	V <sub>GD</sub>	0.1			v	V <sub>D</sub> =480V, Tj=125°C			
Holding current	Iн	2	10.0		mA	R <sub>G-K</sub> =1kΩ, Tj=25°C			
Off-state current (1)	I <sub>DRM</sub> (1)			100	μΑ	V <sub>D</sub> =V <sub>DRM</sub> , R <sub>G-K</sub> =1kΩ, Tj=25°C			
Off-state current (2)	I <sub>DRM</sub> (2)			1	mA	V <sub>D</sub> =V <sub>DRM</sub> , R <sub>G-K</sub> =1kΩ, Tj=125°C			
Thermal resistance	Rth			4.0	°C/W	Junction to case			
Diode forward voltage	VF			1.4	v	IF=10A			



2μs/div